## DATA SHEET

# SILICON TRANSISTOR 2SD2463

## NPN SILICON EPITAXIAL TRANSISTOR FOR LOW-FREQUENCY POWER AMPLIFIERS AND MID-SPEED SWITCHING

The 2SD2463 is a Darlington connection transistor with onchip dumper diode in collector to emitter and zener diode in collector to base. This transistor is ideal for use in acuator drives such as motors, relays, and solenoids.

#### FEATURES

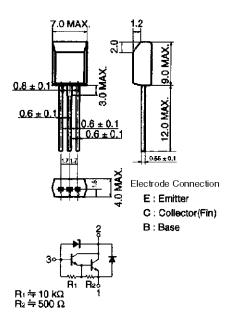
NEC

- Cost reduction available due to on-chip dumper diode (C to E) and zener diode (C to B)
- · Low collector saturation voltage
- Insulation type package supportable for radial taping

#### QUALITY GRADES

Standard

Please refer to "Quality Grades on NEC Semiconductor Devices" (Document No. C11531E) published by NEC Corporation to know the specification of quality grade on the devices and its recommended applications.



PACKAGE DRAWING (UNIT: mm)

Parameter	Symbol	Conditions	Ratings	Unit
Collector to base voltage	Vсво		31±4	V
Collector to emitter voltage	VCEO		31±4	V
Emitter to base voltage	VEBO		8.0	V
Collector current (DC)	IC(DC)	Tc = 25°C	±2.0	А
Collector current (pulse)	C(pulse)	PW $\leq$ 10 ms, Duty cycle $\leq$ 50%, Tc = 25°C	±3.0	А
Base current (DC)	B(DC)		0.2	А
Total power dissipation	Ρτ		1.0	W
Total power dissipation	Ρτ	$T_{C} = 25^{\circ}C$	6.0	W
Junction temperature	Tj		150	°C
Storage temperature	Tstg		–55 to +150	°C

#### ABSOLUTE MAXIMUM RATINGS (Ta = 25°C)

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### ELECTRICAL CHARACTERISTICS (Ta = 25°C)

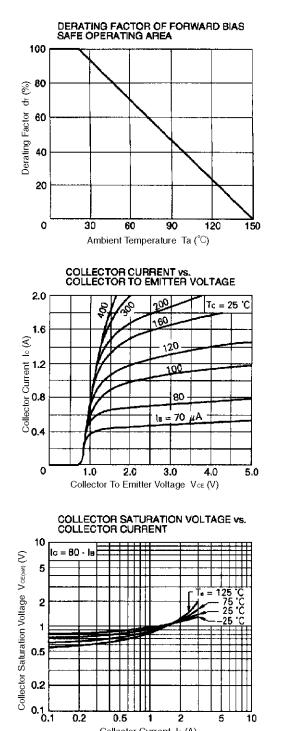
Parameter	Symbol	Conditions		TYP.	MAX.	Unit
Collector cutoff current	Ісво	V <sub>CB</sub> = 20 V, I <sub>E</sub> = 0			10	μA
DC current gain	hfe1	$V_{CE} = 2.0 \text{ V}, \text{ Ic} = 0.5 \text{ A}$	1000			-
DC current gain	hFE2	Vce = 2.0 V, Ic = 1.0 A	2000		30000	-
Collector saturation voltage	VCE(sat)	Ic = 1.0 A, Iв = 1.0 mA		0.9	1.2	V
Base saturation voltage	VBE(sat)	Ic = 1.0 A, Iв = 1.0 mA		1.6	2.0	V
Turn-on time	ton	$\label{eq:lc} \begin{array}{l} lc = 1.0 \text{ A}, \text{ Vcc} = 20 \text{ V} \\ l_{B1} = -l_{B2} = 0.5 \text{ mA} \\ \text{R}_{L} = 20 \ \Omega \end{array}$		0.5		μs
Storage time	tstg			3.0		μs
Turn-off time	tr			1.0		μs

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#### **hfe CLASSIFICATION**

Marking	М	L	К	
hfe2	2000 to 5000	4000 to 10000	8000 to 30000	

#### **TYPICAL CHARACTERISTICS (Ta = 25°C)**



0.2

0.5

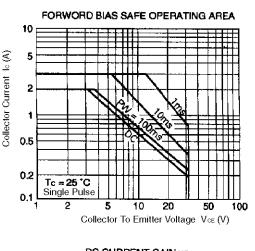
1

Collector Current Ic (A)

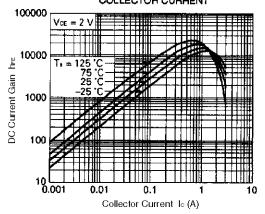
2

5

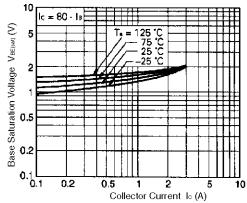
10



DC CURRENT GAIN vs. COLLECTOR CURRENT



BASE SATURATION VOLTAGE vs. COLLECTOR CURRENT



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